

Isc N-Channel MOSFET Transistor

IPB60R199CP

• FEATURES

- With To-263(D2PAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

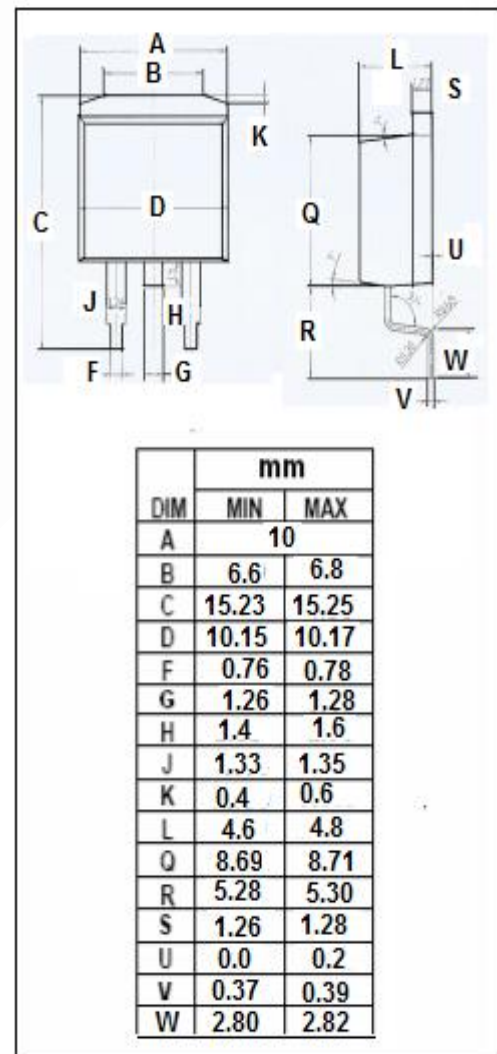
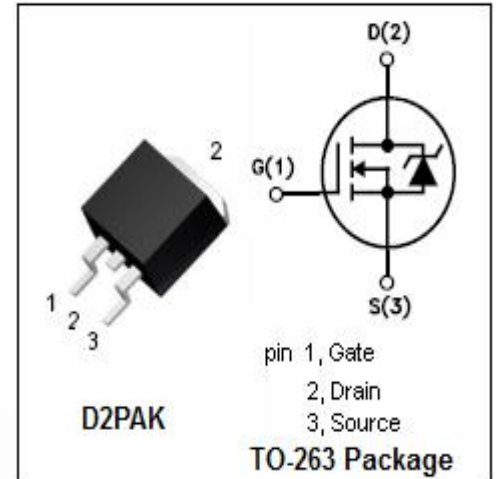
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	16 10	A
I_{DM}	Drain Current-Single Pulsed	51	A
P_D	Total Dissipation @ $T_c=25^{\circ}\text{C}$	139	W
T_{ch}	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.9	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C/W}$



Isc N-Channel MOSFET Transistor**IPB60R199CP****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =1.1mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =9.9A		180	199	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} =0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V; T _j =25°C V _{DS} =600V; V _{GS} = 0V; T _j =150°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =9.9A, V _{GS} = 0 V		0.9	1.2	V